

SPECIFICATION OF LED CHIP

C680-40

[INFRARED]

1) Commodity Type and Physical Characteristics.

- | | | | |
|----------------------|-------------|-------------------|-----------------|
| 1. Material | GaAlAs | | |
| 2. Electrode | Top Side | N (cathode)side | :Au Alloy & Pad |
| | Bottom Side | P (anode)side | :Au Alloy |
| 3. Electrode Pattern | Fig.1 | | |
| 4. Chip Size | Fig.2 | | |
| 5. Chip Thickness | Fig.2 | | |
| 6. Emission Area | Fig.2 | | |

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	min.	typ.	max.	Unit
Forward Voltage	V _f	I _f =20mA		1.8	2.2	V
Reverse Current	I _r	V _r =5V			10	uA
Power Intensity	P _o	I _f =20mA	1.0	2.0		mW
Peak Wavelength	λ _P	I _f =20mA	660	680	700	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		20		nm
Rise Time	t _r	I _f =20mA		80		ns
Full time	t _f	I _f =20mA		80		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit : um]

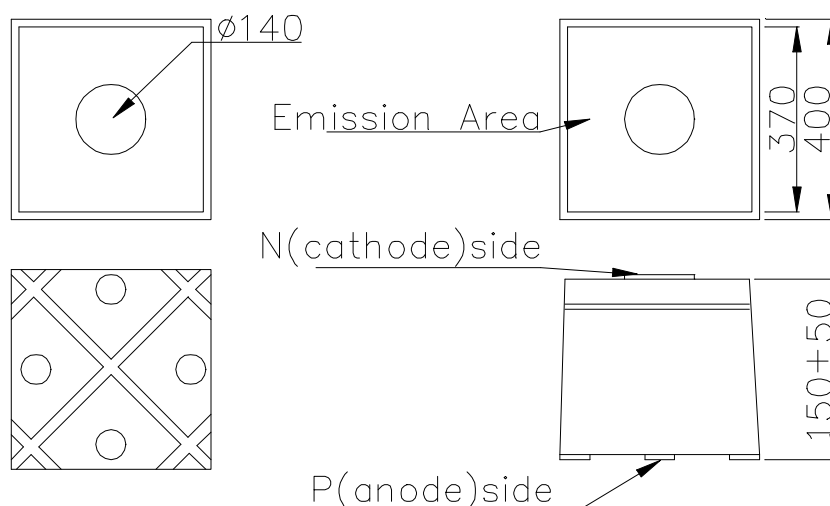


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area